

FDMS6681Z

MOSFET – POWERTRENCH[®], P-Channel

-30 V, -122 A, 3.2 mΩ

General Description

The FDMS6681Z has been designed to minimize losses in load switch applications. Advancements in both silicon and package technologies have been combined to offer the lowest $r_{DS(on)}$ and ESD protection.

Features

- Max $r_{DS(on)}$ = 3.2 mΩ at $V_{GS} = -10$ V, $I_D = -21.1$ A
- Max $r_{DS(on)}$ = 5.0 mΩ at $V_{GS} = -4.5$ V, $I_D = -15.7$ A
- Advanced Package and Silicon Combination for Low $r_{DS(on)}$
- HBM ESD Protection Level of 8 kV Typical (Note 3)
- MSL1 Robust Package Design
- RoHS Compliant

Applications

- Load Switch in Notebook and Server
- Notebook Battery Pack Power Management

MOSFET MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Unit
V_{DS}	Drain to Source Voltage	-30	V
V_{GS}	Gate to Source Voltage	±25	V
I_D	Drain Current – Continuous $T_C = 25^\circ\text{C}$ (Note 5)	-122	A
	– Continuous $T_C = 100^\circ\text{C}$ (Note 5)	-77	
	– Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	-21.1	
	– Pulsed (Note 4)	-600	
P_D	Power dissipation $T_C = 25^\circ\text{C}$	73	W
	Power dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.5	
T_J , T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

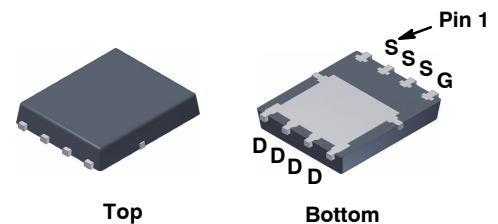
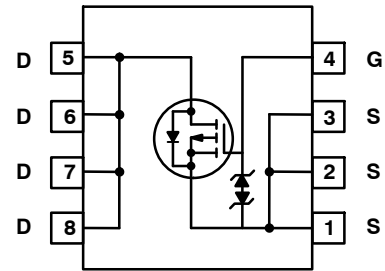
THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.7	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	



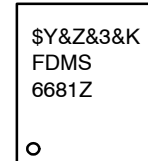
ON Semiconductor[®]

www.onsemi.com



Power 56 (PQFN8)
CASE 483AE

MARKING DIAGRAM



\$Y = ON Semiconductor Logo
 &Z = Assembly Plant Code
 &3 = Numeric Date Code
 &K = Lot Code
 FDMS6681Z = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FDMS6681Z

PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Package	Shipping [†]
FDMS6681Z	FDMS6681Z	Power 56	3000 Units/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
--------	-----------	-----------------	-----	-----	-----	------

OFF CHARACTERISTICS

BV _{DSS}	Drain to Source Breakdown Voltage	I _D = -250 μA, V _{GS} = 0 V	-30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = -250 μA, referenced to 25°C		20		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -24 V, V _{GS} = 0 V			-1	μA
I _{GSS}	Gate to Source Leakage Current	V _{GS} = ±25 V, V _{DS} = 0 V			±10	μA

ON CHARACTERISTICS

V _{GS(th)}	Gate to Source Threshold Voltage	V _{GS} = V _{DS} , I _D = -250 μA	-1	-1.7	-3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I _D = -250 μA, referenced to 25°C		-7		mV/°C
r _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = -10 V, I _D = -22.1 A		2.7	3.2	mΩ
		V _{GS} = -4.5 V, I _D = -15.7 A		4.0	5.0	
		V _{GS} = -10 V, I _D = -22.1 A, T _J = 125°C		3.9	5.0	
g _{FS}	Forward Transconductance	V _{DD} = -10 V, I _D = -22.1 A		143		S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = -15 V, V _{GS} = 0 V, f = 1MHz		7803	10380	pF
C _{oss}	Output Capacitance			1540	2050	
C _{rss}	Reverse Transfer Capacitance			1345	2020	

SWITCHING CHARACTERISTICS

t _{d(on)}	Turn – On Delay Time	V _{DD} = -15 V, I _D = -22.1 A, V _{GS} = -10 V, R _{GEN} = 6 Ω		15	24	ns
t _r	Rise Time			38	61	
t _{d(off)}	Turn – Off Delay Time			260	416	
t _f	Fall Time			197	316	
Q _g	Total Gate Charge	V _{GS} = 0 V to -10 V	V _{DD} = -15 V, I _D = -22.1 A	172	241	nC
Q _g	Total Gate Charge	V _{GS} = 0 V to -5 V		97	136	
Q _{gs}	Gate to Source Charge			22		
Q _{gd}	Gate to Drain “Miller” Charge			46		

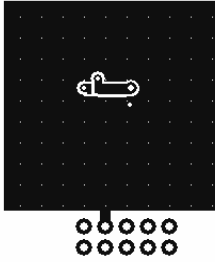
DRAIN-SOURCE DIODE CHARACTERISTICS

V _{SD}	Source to Drain Diode Forward Voltage	V _{GS} = 0 V, I _S = -2.1 A (Note 2)		0.68	1.2	V
		V _{GS} = 0 V, I _S = -22.1 A (Note 2)		0.79	1.25	
t _{rr}	Reverse Recovery Time	I _F = -22.1 A, di/dt = 100 A/μs		44	71	ns
Q _{rr}	Reverse Recovery Charge			39	63	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50°C/W when mounted on a 1 in² pad of 2 oz copper.



b) 125°C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.
4. Pulsed I_D please refer to Figure 12 SOA graph for more details.
5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal electro-mechanical application board design.

TYPICAL CHARACTERISTICS $T_J = 25^\circ\text{C}$ unless otherwise noted

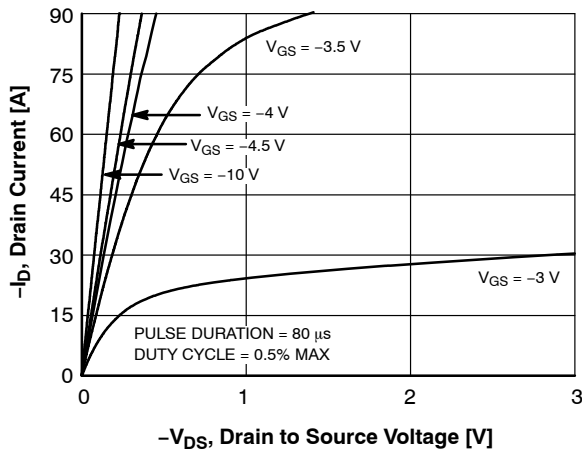


Figure 1. On Region Characteristics

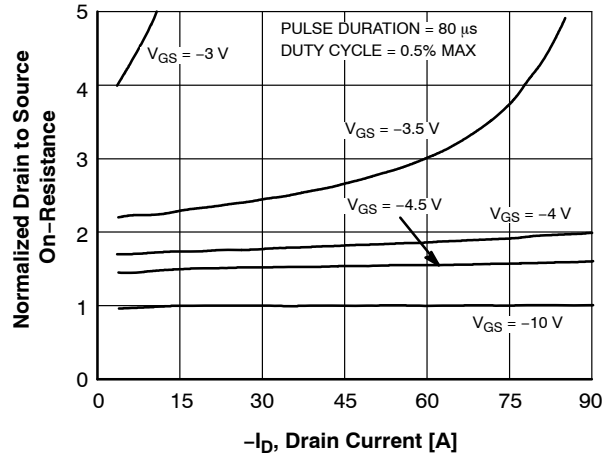


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

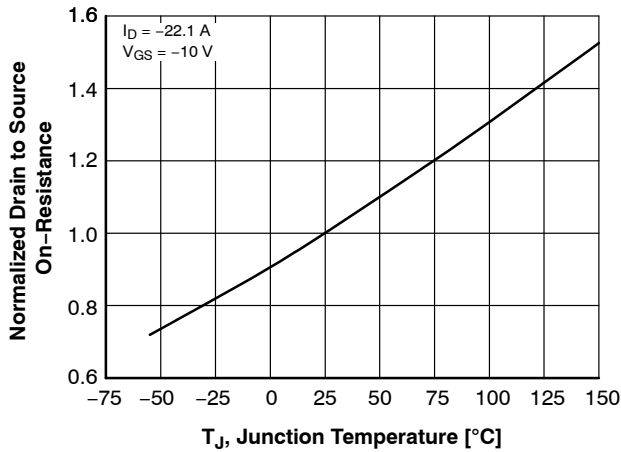


Figure 3. Normalized On Resistance vs. Junction Temperature

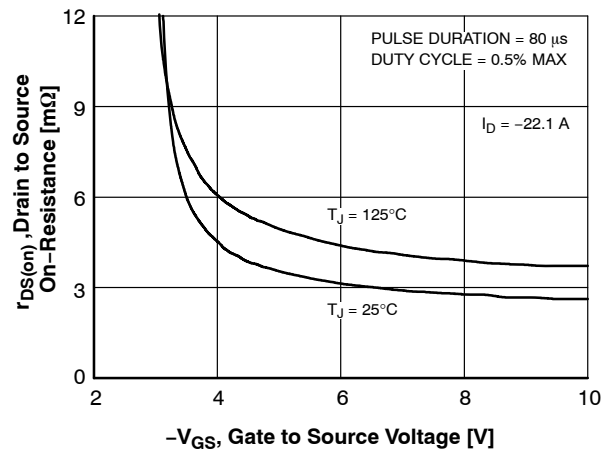


Figure 4. On-Resistance vs. Gate to Source Voltage

TYPICAL CHARACTERISTICS $T_J = 25^\circ\text{C}$ unless otherwise noted (continued)

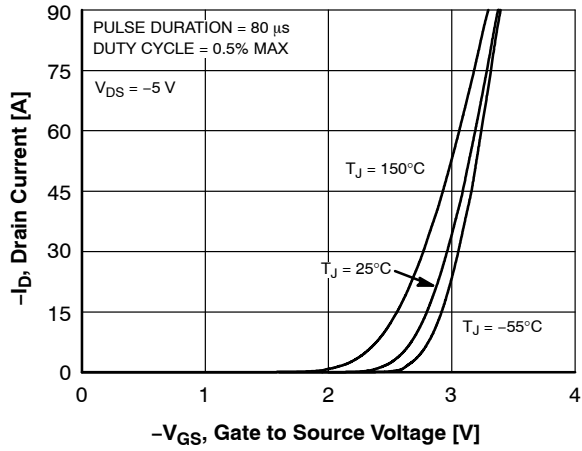


Figure 5. Transfer Characteristics

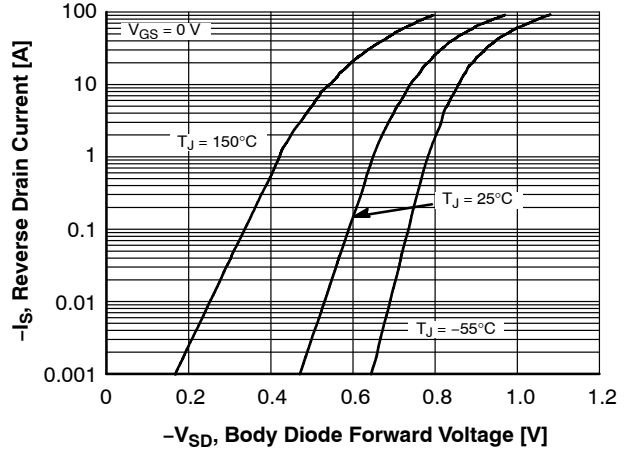


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

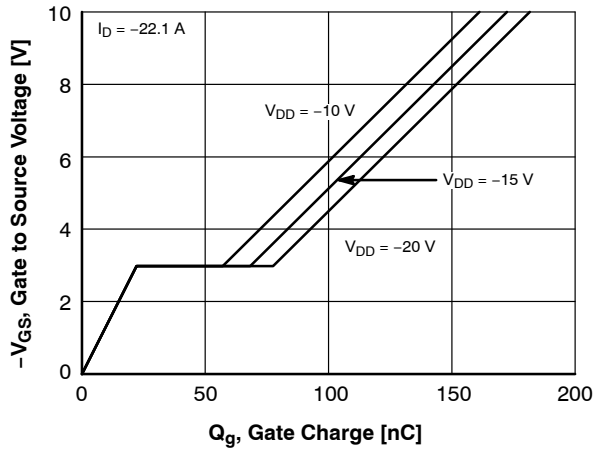


Figure 7. Gate Charge Characteristics

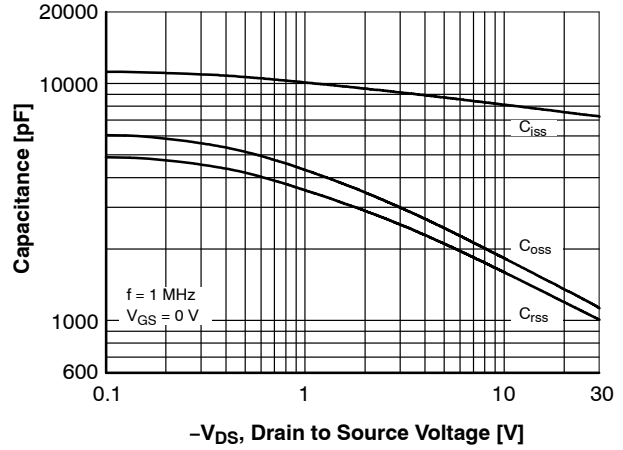


Figure 8. Capacitance vs. Drain to Source Voltage

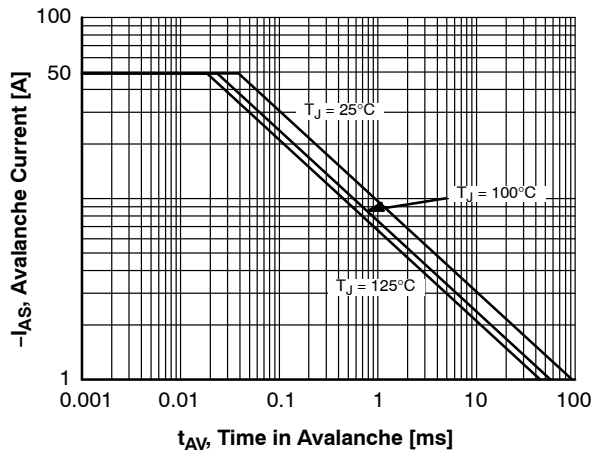


Figure 9. Unclamped Inductive Switching Capability

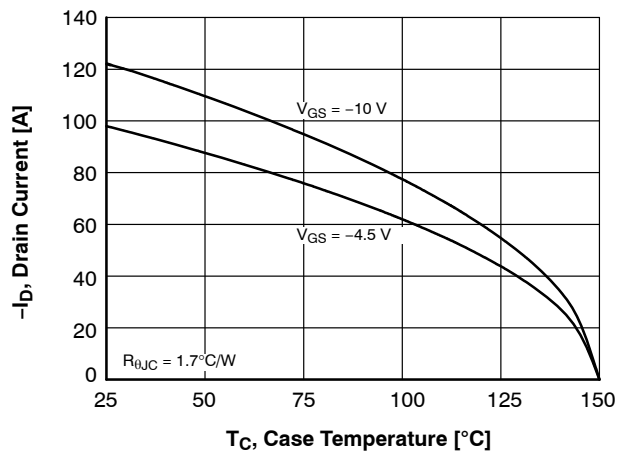


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

TYPICAL CHARACTERISTICS $T_J = 25^\circ\text{C}$ unless otherwise noted (continued)

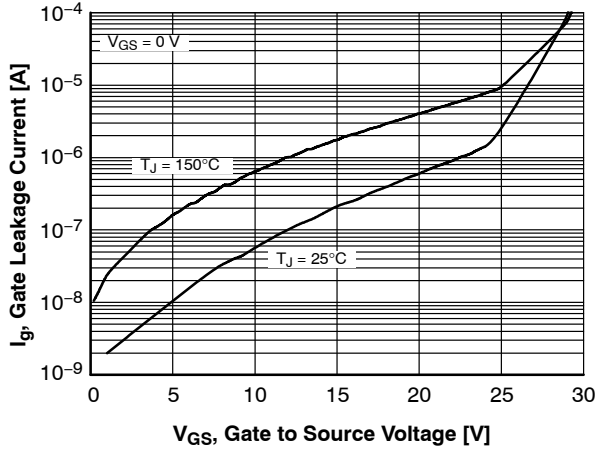


Figure 11. I_{gss} vs. V_{gss}

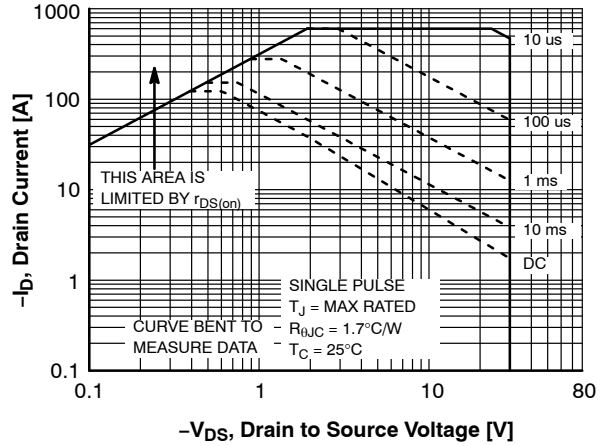


Figure 12. Forward Bias Safe Operating Area

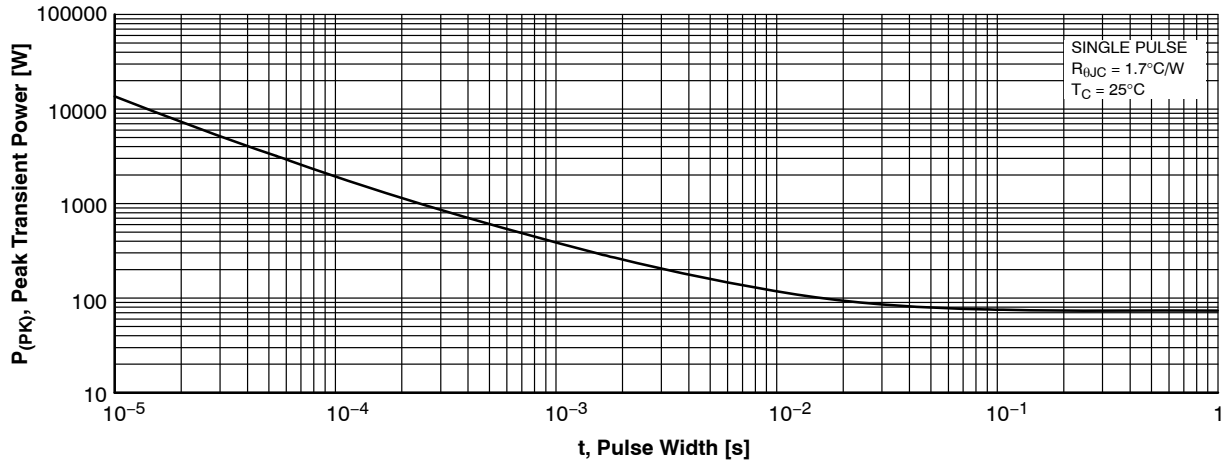


Figure 13. Single Pulse Maximum Power Dissipation

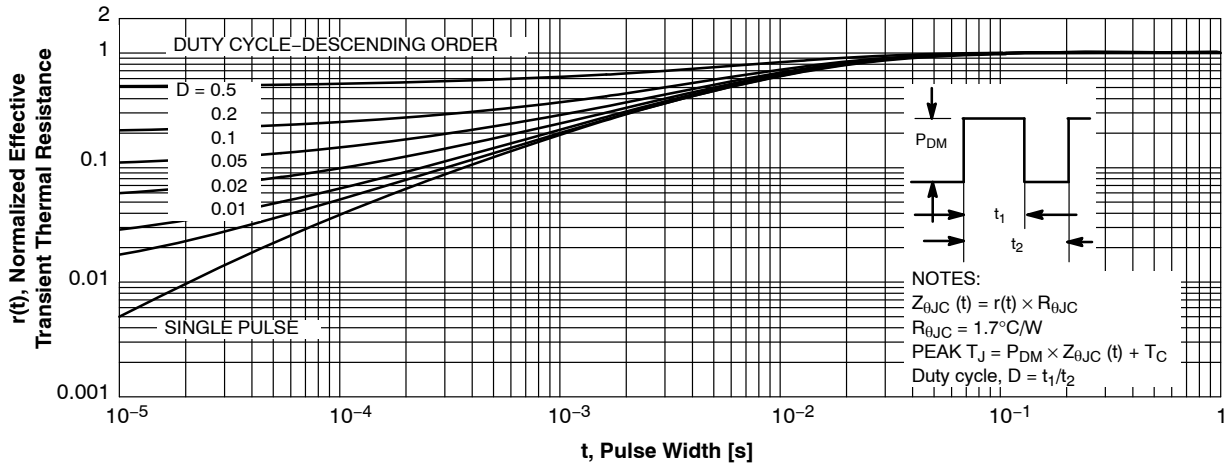


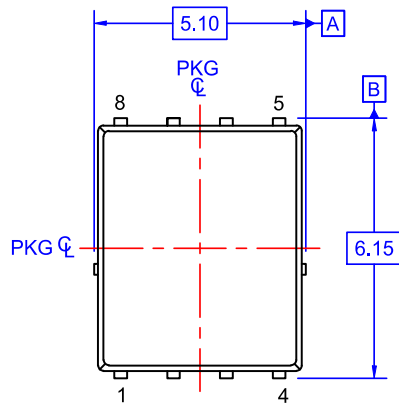
Figure 14. Transient Thermal Response Curve

POWERTRENCH is registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries.

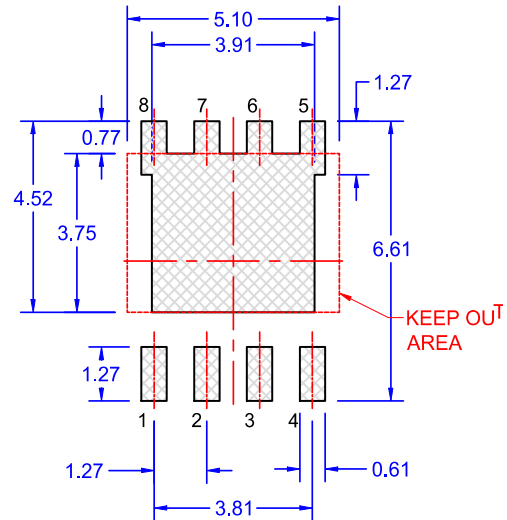
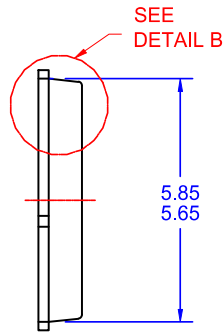


PQFN8 5X6, 1.27P
CASE 483AE
ISSUE A

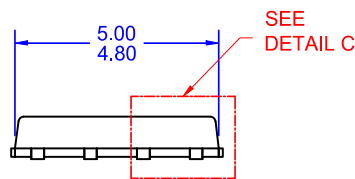
DATE 27 SEP 2017



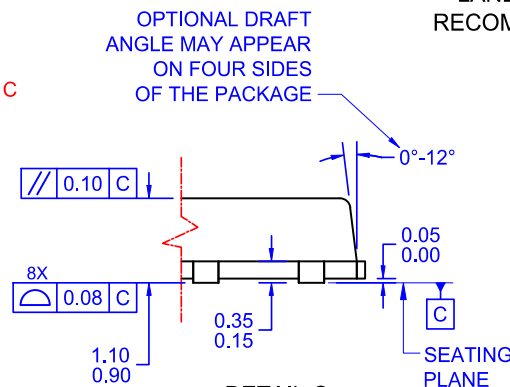
TOP VIEW



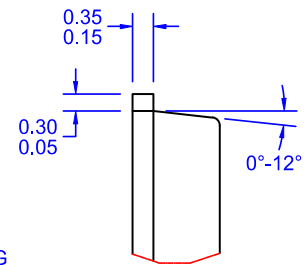
LAND PATTERN
 RECOMMENDATION



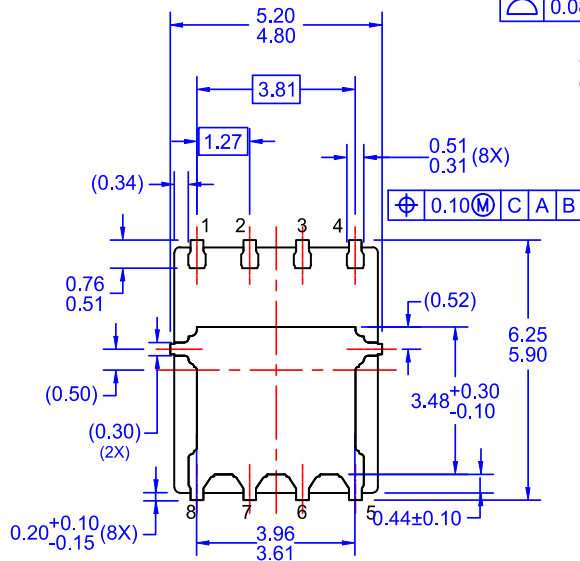
SIDE VIEW



DETAIL C
 SCALE: 2:1



DETAIL B
 SCALE: 2:1



- NOTES: UNLESS OTHERWISE SPECIFIED
- A. PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. AA,.
 - B. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
 - C. ALL DIMENSIONS ARE IN MILLIMETERS.
 - D. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
 - E. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.

DOCUMENT NUMBER:	98AON13655G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	PQFN8 5X6, 1.27P	PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local
Sales Representative